

GP2S04/GP2S06/GP2S07 /GP2S09/GP2S10

Subminiature PhotoInterrupter

■ Features

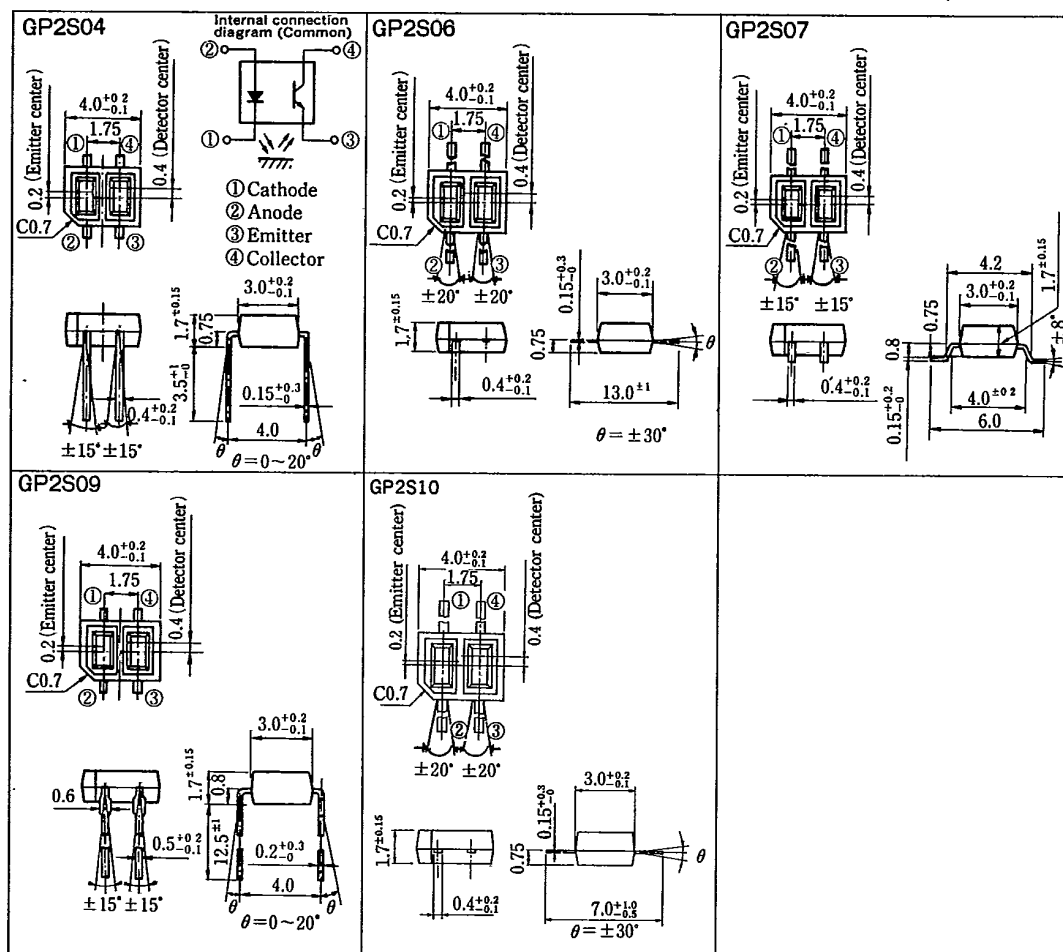
1. Compact and thin
GP2S04 : Compact DIP type
GP2S06 : Flat lead type
GP2S07 : Mini-flat package type
GP2S09 : Compact DIP, long lead type
GP2S10 : Short flat lead type
2. Optical detection distance : 0.8~1mm
3. Visible light cut-off type

■ Applications

1. Cassette tape recorders, VCRs
2. Floppy disk drives
3. Various microcomputerized control equipment

■ Outline Dimensions

(Unit : mm)



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■ Absolute Maximum Ratings

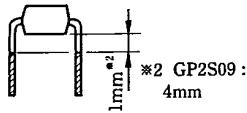
(Ta=25°C)

Parameter	Symbol	Rating	Unit
Input	Forward current	I_F	50 mA
	Reverse voltage	V_R	6 V
	Power dissipation	P_D	75 mW
Output	Collector-emitter voltage	V_{CE0}	35 V
	Emitter-collector voltage	V_{ECO}	6 V
	Collector current	I_C	20 mA
	Collector power dissipation	P_C	75 mW
	Total power dissipation	P_{tot}	100 mW
Operating temperature		T_{opr}	-25 ~ +85 °C
Storage temperature		T_{stg}	-40 ~ +100 °C
*1 Soldering temperature		T_{sol}	260 °C

*1 Within 5 seconds (Soldering areas for each model are shown below.)

GP2S04, GP2S09

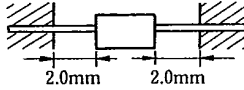
Soldering area

The hatched area more than 1mm² away from the lower edge of package as shown in the figure below.

GP2S06

Soldering area

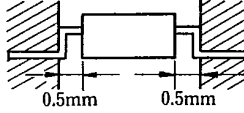
The hatched area more than 2.0mm away from the both edges of package as shown in the figure below.



GP2S07

Soldering area

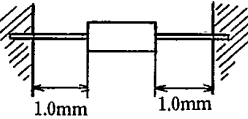
The hatched area more than 0.5mm away from the both edges of package as shown in the figure below.



GP2S10

Soldering area

The hatched area more than 1.0mm away from the both edges of package as shown in the figure below.



■ Electro-optical Characteristics

(Ta=25°C)

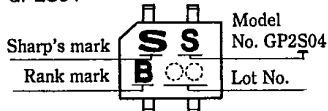
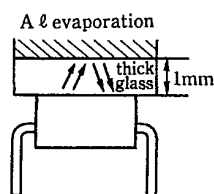
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input	Forward voltage	V_F	$I_F=20\text{mA}$	—	1.2	1.4 V
	Reverse current	I_R	$V_R=6\text{V}$	—	10	μA
Output	Collector dark current	I_{CE0}	$V_{CE}=20\text{V}$	—	1×10^{-9}	1×10^{-7} A
	*3 Collector current	I_C	$I_F=4\text{mA}, V_{CE}=2\text{V}$	20	45	120 μA
Transfer characteristics	Response time (Rise)	t_r	$V_{CE}=2\text{V}, I_C=100\mu\text{A}$	—	20	100 μs
	Response time (Fall)	t_f	$R_L=1\text{k}\Omega, d=1\text{mm}$	—	20	100 μs
	*4 Leak current	I_{LEAK}	$I_F=4\text{mA}, V_{CE}=2\text{V}$	—	—	0.1 μA

*3 The condition and arrangement of the reflective object are shown in the right drawing.

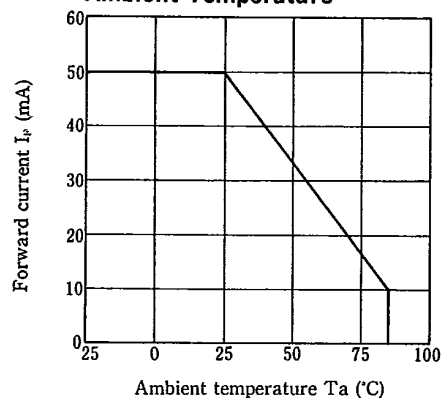
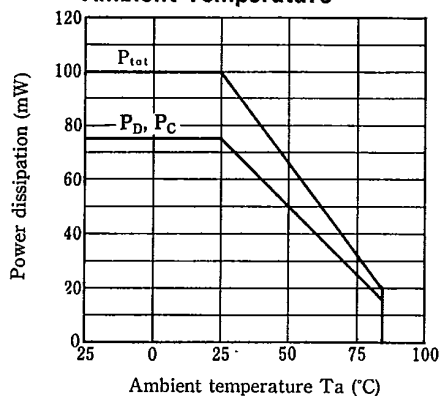
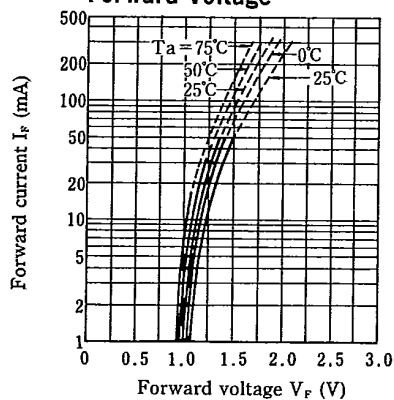
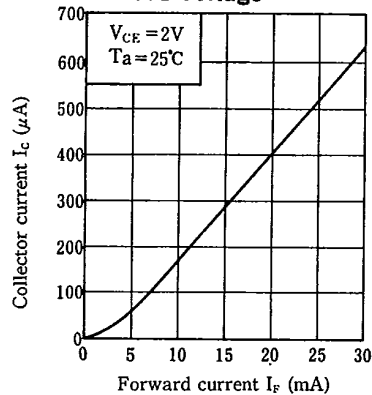
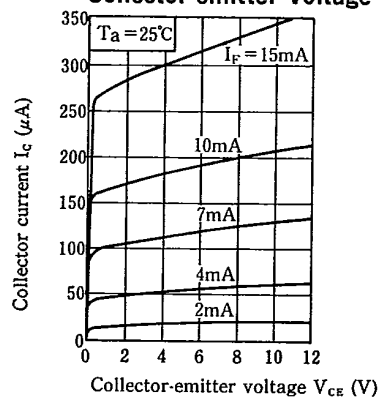
*4 Without reflective object

The ranking of collector current shall be classified into the following 6 ranks.
(GP2S04, GP2S06, GP2S07, GP2S09)

Rank	I_C (μA)	Rank mark
A	20~42	A
B	34~71	B
C	58~120	C
A or B	20~71	A or B
B or C	34~120	B or C
A, B or C	20~120	A, B or C

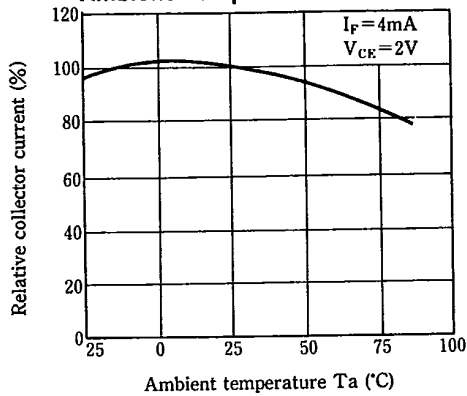
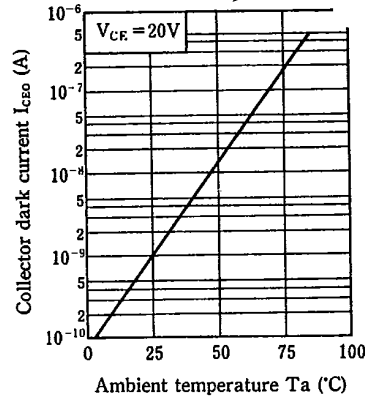
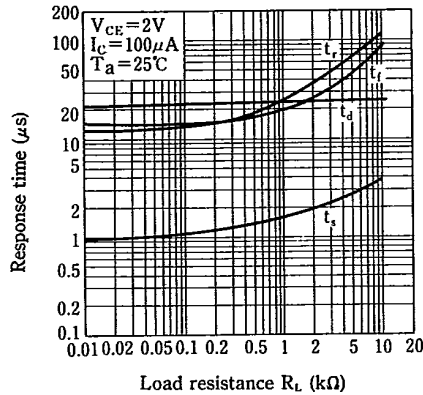
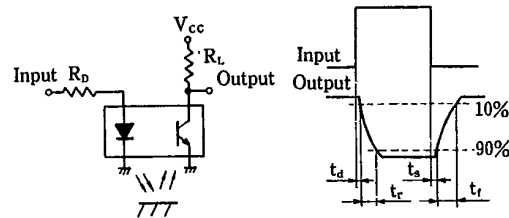
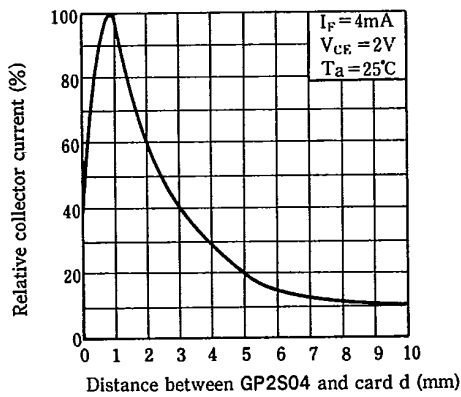
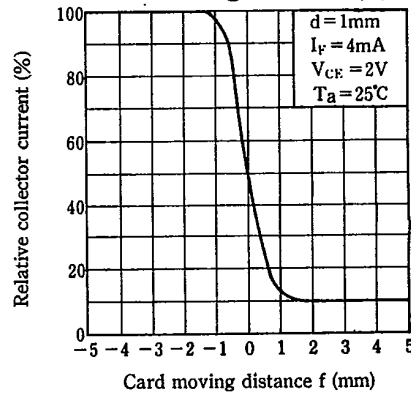
Marking example
GP2S04Test Condition and
Arrangement for
Collector Current

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Fig. 1 Forward Current vs.
Ambient TemperatureFig. 2 Power Dissipation vs.
Ambient TemperatureFig. 3 Forward Current vs.
Forward VoltageFig. 4 Collector Current vs.
Forward VoltageFig. 5 Collector Current vs.
Collector-emitter Voltage

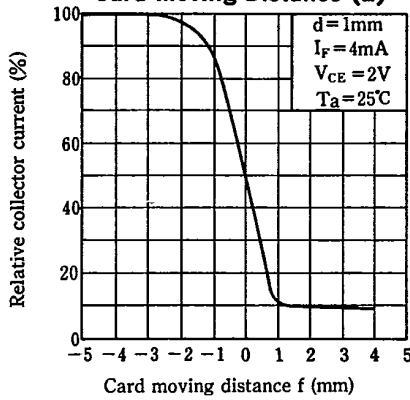
Photointerrupters

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Fig. 6 Relative Collector Current vs. Ambient Temperature**Fig. 7 Collector Dark Current vs. Ambient Temperature****Fig. 8 Response Time vs. Load Resistance****Test Circuit for Response Time****Fig. 9 Relative Collector Current vs. Distance between GP2S04 and Card****Fig. 10 Relative Collector Current vs. Card Moving Distance (1)**

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Fig. 11 Relative Collector Current vs. Card Moving Distance (2)



Test Condition for Distance & Detecting Position Characteristics

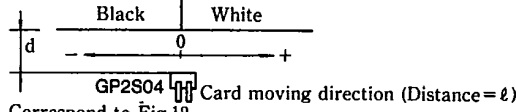
Correspond to Fig.10

SHARP OMS TEST CARD (White)

T-41-73

Correspond to Fig.11

SHARP OMS TEST CARD



Correspond to Fig.12

SHARP OMS TEST CARD

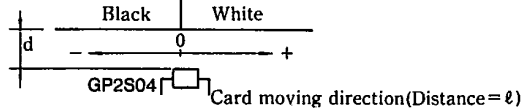


Fig. 12 Frequency Response

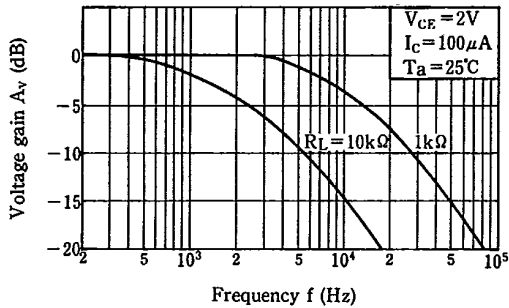


Fig. 13 Spectral Sensitivity (Detecting Side)

